

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-4 (Canceled)

Claim 5 (Previously Presented): The semiconductor device according to Claim 16, wherein

said first, fourth, second and third semiconductor layers are adjacent to each other in this order, and

said first and third semiconductor layers function as source/drain layers of MOS transistors having conductivity types different from each other, respectively.

Claim 6 (Previously Presented): The semiconductor device according to Claim 16, further comprising a cover having an insulative surface in contact with said portion of said pn junction separated from said isolator.

Claim 7 (Original): The semiconductor device according to Claim 5, further comprising

a cover having a insulative surface in contact with said portion of said pn junction separated from said isolator.

Claims 8-15 (Canceled).

Claim 16 (Currently Amended): A semiconductor device comprising:
a substrate at least having an insulative surface;

a semiconductor film provided on said surface of said substrate comprising a first semiconductor layer of a first conductivity type, a second semiconductor layer of said first conductivity type having an impurity concentration lower than that of said first semiconductor layer, a third semiconductor layer of a second conductivity type opposite to said first conductivity type and a fourth semiconductor layer of said second conductivity type having an impurity concentration lower than that of said third semiconductor layer; and

an insulative isolator formed on a surface of said semiconductor film on the far side from said substrate, separately from said surface of said substrate, wherein

said second and fourth semiconductor layers form a pn junction extending in the thickness direction of said semiconductor film, said pn junction has a portion separated from said isolator, and

a maximum value of a distance parallel to said surface of said substrate between said pn junction and ~~a boundary between said isolator and said semiconductor film~~ an end of the isolator is not more than $2\mu\text{m}$, when a direction from said ~~boundary to said isolator along end of the isolator toward the isolator in parallel to said surface of said substrate~~ is taken as a positive direction.